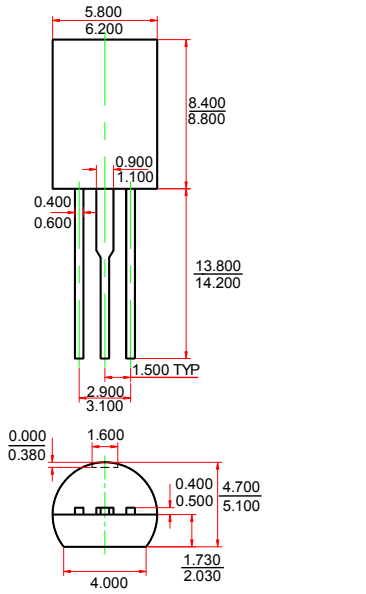
2SA1145

TO-92MOD Transistor (PNP)

1. EMITTER
2. COLLECTOR
3. BASE

TO-92MOD



Dimensions in inches and (millimeters)

Features

- ✧ Complementary to 2SC2705
- ✧ Small collector output capacitance: C_{ob}=2.5pF(Typ.)
- ✧ High transition frequency: f_T=200MHz(Typ.)

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-150	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-50	mA
P_C	Collector Power Dissipation	800	mW
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100 μA, I_E=0	-150			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA, I_B=0	-150			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-100 μA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-150 V, I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-5 V, I_C=0			-0.1	μA
DC current gain	h_{FE}	V_{CE}=-5 V, I_C=-10mA	80		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-10mA, I_B=-1mA			-1	V
Base-emitter voltage	V_{BE}	V_{CE}=-5 V, I_C=-10mA			-0.8	V
Transition frequency	f_T	V_{CE}=-5 V, I_C=-10mA		200		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10 V, I_E=0, f=1 MHz		2.5		pF

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	80-160	120-240
Marking		

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Typical Characteristics